DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2KV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

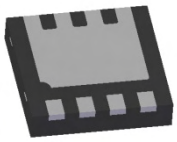
Mechanical Data

- Case: U-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208 e4
- Polarity: See Diagram
- Weight: 0.0172 grams (approximate)



ESD PROTECTED TO 2kV

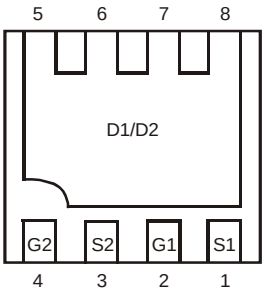
U-DFN3030-8



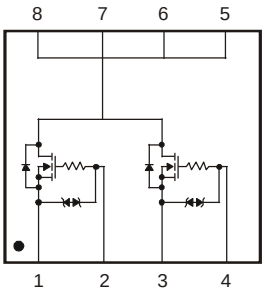
Top View



Bottom View



Bottom View
Pin Configuration



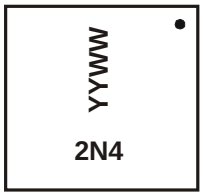
Top View
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG8601UFG-7	U-DFN3030-8	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



2N4 = Product marking code
YYWW = Date code marking
YY = Last digit of year (ex: 09 for 2009)
WW = Week code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +70°C	I_D	6.1 5.2	A
Pulsed Drain Current			I_{DM}	27	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.92	W
Thermal Resistance, Junction to Ambient @T_A = +25°C	$R_{\theta JA}$	136	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = 25°C	I_{DSS}	-	-	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±10	µA	V_{GS} = ±10V, V_{DS} = 0V
Gate-Source Breakdown Voltage	BV_{SGS}	±12	-	-	V	V_{DS} = 0V, I_G = ±250µA
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.35	-	1.05	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	- - -	17 20 25	23 27 34	mΩ	V_{GS} = 4.5V, I_D = 6.5A V_{GS} = 2.5V, I_D = 5.5A V_{GS} = 1.8V, I_D = 3.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	10	-	S	V_{DS} = 10V, I_D = 5A
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	-	143	-	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	74	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	29	-	pF	
Gate Resistance	R_g	-	202	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	-	8.8	-	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A
Gate-Source Charge	Q_{gs}	-	1.4	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.0	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	53	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 10Ω, R_G = 6Ω
Turn-On Rise Time	t_r	-	78	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	562	-	ns	
Turn-Off Fall Time	t_f	-	234	-	ns	

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
6. Short duration pulse test used to minimize self-heating effect.

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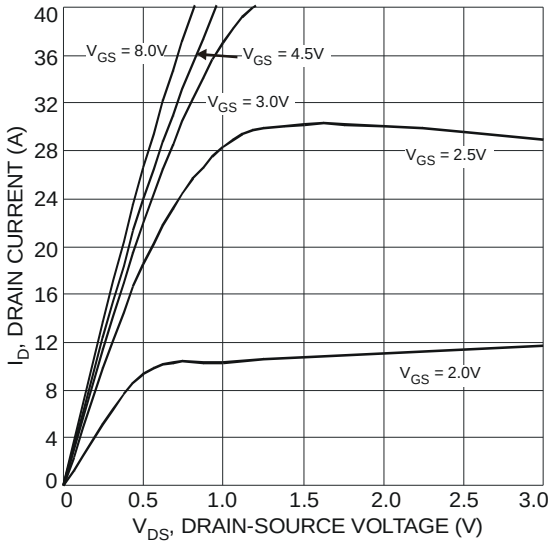


Fig. 1 Typical Output Characteristic

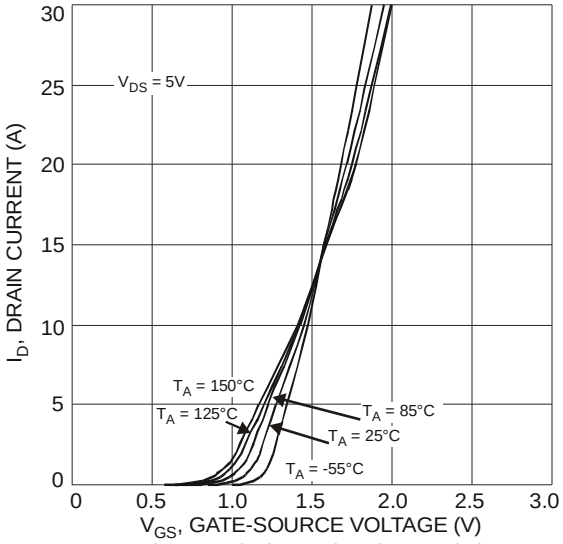


Fig. 2 Typical Transfer Characteristic

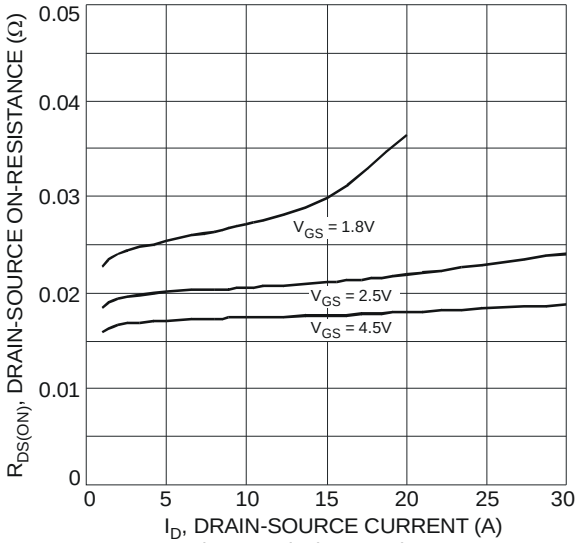


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

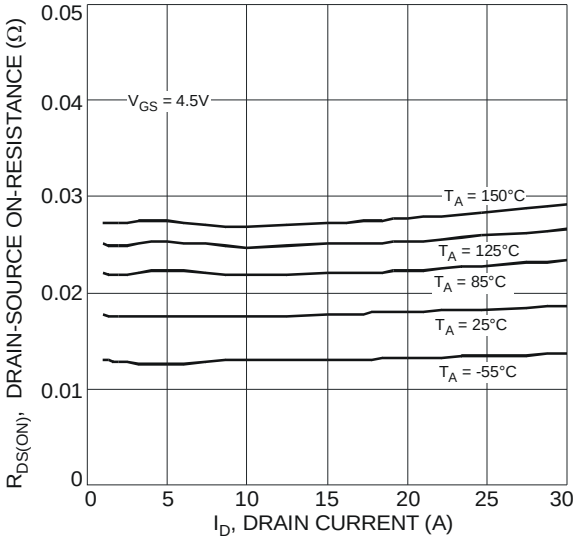


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

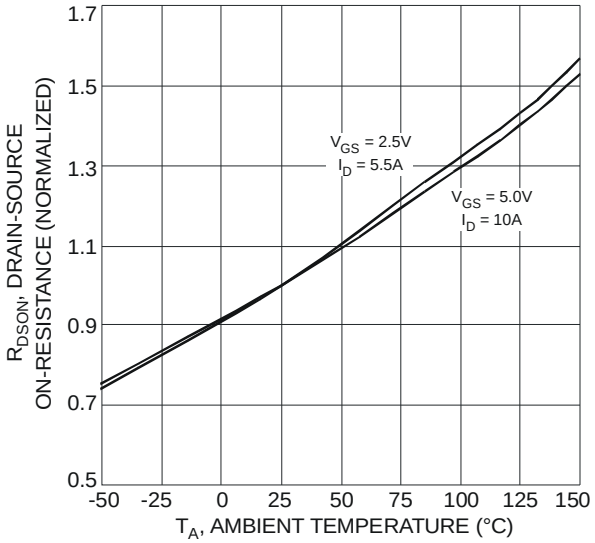


Fig. 5 On-Resistance Variation with Temperature

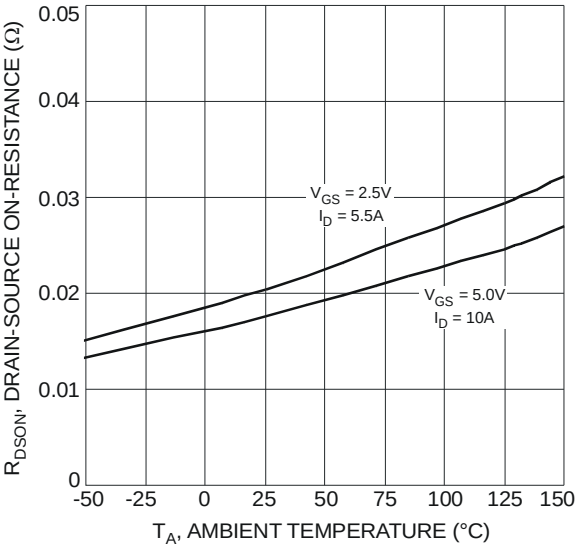


Fig. 6 On-Resistance Variation with Temperature

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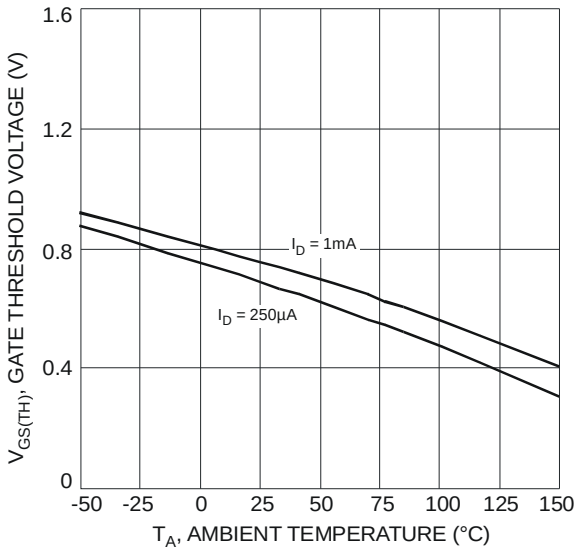


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

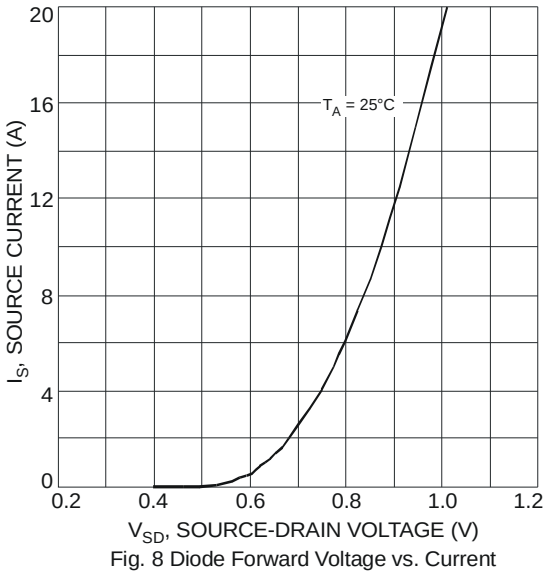


Fig. 8 Diode Forward Voltage vs. Current

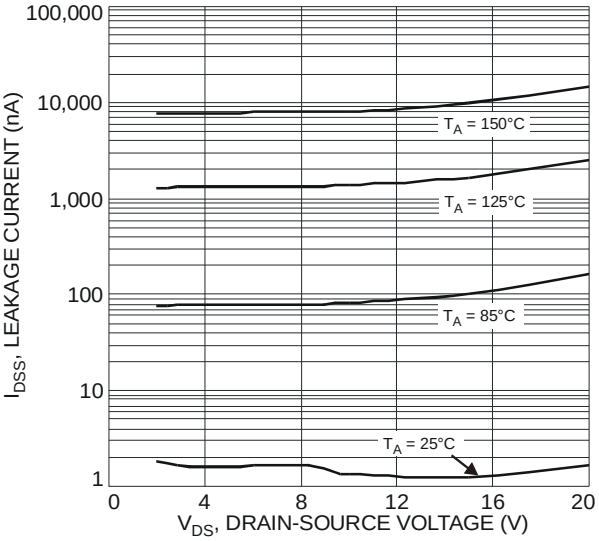


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

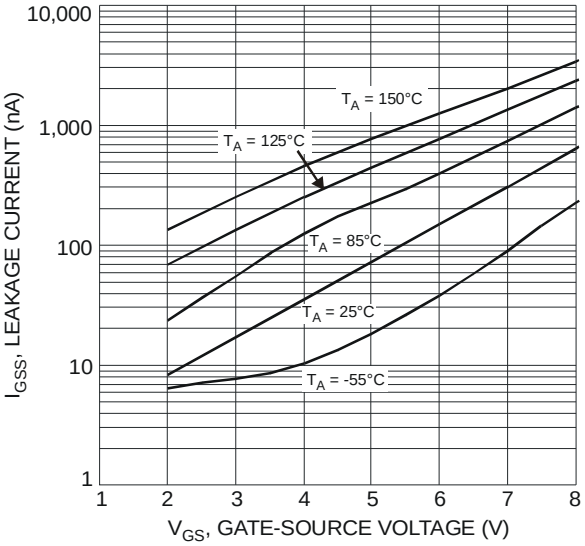


Fig. 10 Gate-Source Leakage Current vs. Voltage

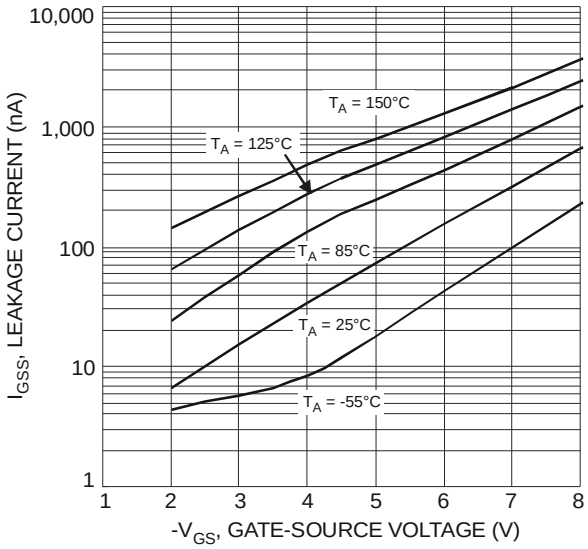


Fig. 11 Gate-Source Leakage Current vs. Voltage

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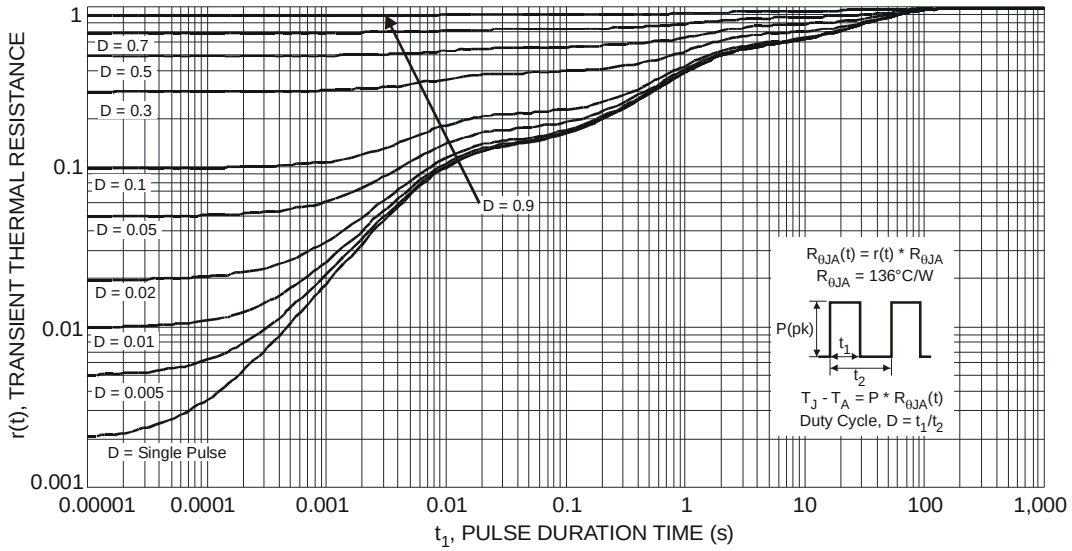
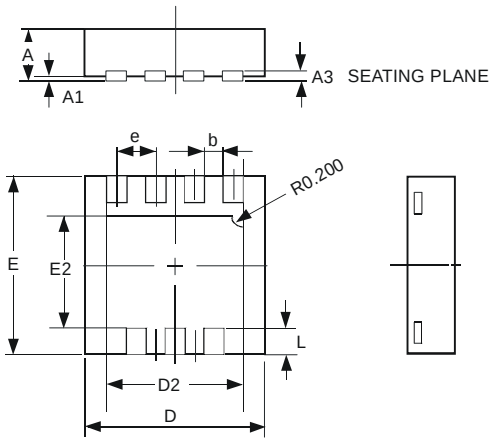


Fig. 12 Transient Thermal Response

Package Outline Dimensions

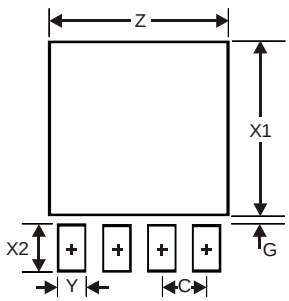
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN3030-8			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0	0.05	0.02
A3	—	—	0.15
b	0.29	0.39	0.34
D	2.90	3.10	3.00
D2	2.19	2.39	2.29
e	—	—	0.65
E	2.90	3.10	3.00
E2	1.64	1.84	1.74
L	0.30	0.60	0.45
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Y	0.39
C	0.65

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